

Title of Change:	Datasheet update to add Transient Vgs of Maximum Ratings
Effective date:	29 Jun 2026
Contact information:	Contact your local onsemi Sales Office
Type of notification:	This Product Bulletin is for notification purposes only. onsemi will proceed with implementation of this change upon publication of this Product Bulletin.
Change Category:	Datasheet update
Change Sub-Category(s):	Datasheet/Product Doc change

Sites Affected:

onsemi Sites	External Foundry/Subcon Sites
None	None

Description and Purpose:

onsemi wishes to inform customers of its plan to update the datasheet for SiC 650V MOSFET discrete products by adding a Gate-to-Source transient voltage parameter under maximum ratings. This update is based on extended reliability validation results, specifically Dynamic Gate Stress(DGS) testing, to better reflect the device capability and operational limits.

1) MAXIMUM RATINGS

Parameter		Symbol	Value		Unit
			Current	Updated	
Gate-to-Source Transient Voltage	tp<0.5us, Duty Cycle≤1%	V _{gs}	NA	-11/25	V

The change will not impact form, fit, or function of products.

List of Affected Standard Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

NVH4L016N065M3S	NVH4L012N065M3S	
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